

AMENDMENTS TO THE SPECIFICATION

Please amend the paragraph on page 1, line 2, to line 3, as follows:

This is a Divisional Application of U.S. Patent Application Serial No. 09/545,504, filed April 7, 2000, which is now U.S. Patent No. 6,667,238, issued December 23, 2003.

Please amend paragraph [0007] on page 3, as follows:

[0007] Immediately after the copper layer is polished in the CMP process, a polished surface of the copper layer on the semiconductor wafer has a high activity so that the polished surface is liable to be oxidized. If the polished surface on the semiconductor wafer is left as it is, then an oxide film is formed by natural oxidation on the polished surface of the semiconductor wafer. However, such oxide film tends to be formed irregularly or nonuniformly because no control is ~~not~~ made of formation of the oxide film, and hence the formed oxide film is of poor quality. If the oxide film is left as it is, then oxidation of the polished surface of the semiconductor wafer is further ~~being~~ developed. Particularly, in the case where copper is used as a material for forming a wiring circuit of a semiconductor device, electrical characteristics are changed to produce products inferior in quality.

Please amend paragraph [0010] on page 3, as follows:

[0010] According to one aspect of the present invention, there is provided a polishing apparatus comprising a polishing section having a turntable with a polishing surface and a top ring for holding a substrate and pressing the substrate against the polishing surface to polish a surface having a semiconductor device thereon. A cleaning section cleans the substrate which has been polished, the cleaning section having an electrolyzed water supply device for supplying electrolyzed water to the substrate to clean at least a polished surface of the substrate while supplying the electrolyzed water to the substrate. As electrolyzed water, anode electrolyzed water is desirable. The turntable preferably comprises a ceramic turntable.

Please amend paragraph [0036] on page 9, as follows:

[0036] FIG. 4 is a schematic side view showing the structure of the cleaning units 7a, 7b. As shown in FIG. 4, each of the cleaning units 7a and 7b comprises a plurality of rollers 23 for holding the peripheral edge of the semiconductor wafer 20 and rotating the semiconductor wafer 20 in a horizontal plane, PVA (polyvinyl alcohol) sponge cleaning members 24a, 24b having a cylindrical shape for contacting and scrubbing the front and back surfaces of the semiconductor wafer 20, electrolyzed water supply nozzles 25a, 25b disposed above and below the semiconductor wafer 20, and DHF supply nozzles 26a, 26b disposed above and below the semiconductor wafer 20. An ultrasonic transducer 26 is provided in each of the lines of the electrolyzed water supply nozzles 25a, 25b. The electrolyzed water supply nozzles 25a, 25b supply anode electrolyzed water to the semiconductor wafer, and the DHF supply nozzles 26a, 26b supply DHF (diluted hydrofluoric acid) to the semiconductor wafer. At least one of the electrolyzed water supply nozzles 25a, 25b constitutes an electrolyzed water supply device, and at least one of the DHF supply nozzles 26a, 26b constitutes a supply device for supplying diluted hydrofluoric acid. The ultrasonic transducer 26 imparts ultrasonic vibrations to the anode electrolyzed water to produce megasonic anode electrolyzed water. It is desirable to produce electrolyzed water at a place as close as possible to the electrolyzed water ~~ionic wafer~~ supply nozzles 25a, 25b for thereby lengthening life of the electrolyzed water, i.e., preventing a change of concentration of the electrolyzed water. Further, it is desirable to install a measuring device and/or a controller for monitoring and/or controlling characteristic values such as pH or ion concentration in an electrolyzed water generator.